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Optoelectronics Division
TRW Electronic Components Group

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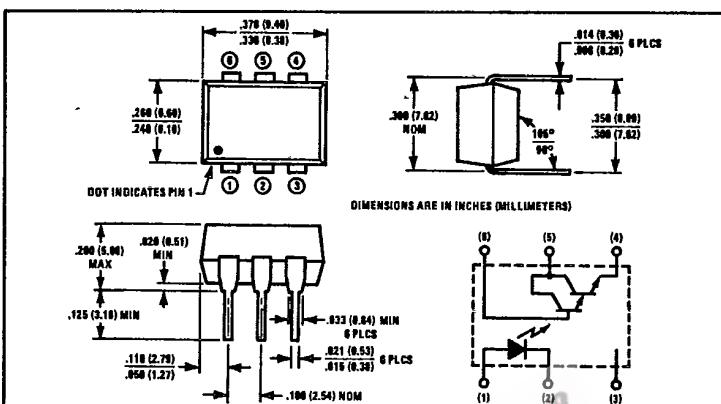
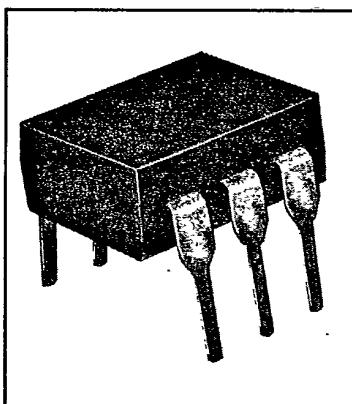


Product Bulletin 5226
January 1988

T-41-85

Optically Coupled Isolators

Types OPI3153, OPI3253



Features

- Photodarlington output
- High current transfer ratio
- 2500 or 1500 volt isolation ratings
- UL recognized File No. E58730

Description

The OPI3153 and OPI3253 are optically coupled isolators each consisting of a gallium arsenide infrared emitting diode and an NPN silicon photodarlington mounted in a standard plastic six pin dual-in-line package. Except for isolation voltage, the OPI3153 and OPI3253 are identical.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Input-to-Output Isolation Voltage -- OPI3153	$\pm 1500 \text{ VDC}^{(1)}$
OPI3253	$\pm 2500 \text{ VDC}^{(1)}$
Storage Temperature Range	-55°C to $+150^\circ\text{C}$
Operating Temperature Range	-55°C to $+100^\circ\text{C}$
Lead Soldering Temperature (1/16 inch [1.6 mm] from case for 5 sec. with soldering iron) ⁽²⁾	260°C
Input Diode		
Forward DC Current80 mA
Peak Forward Current (1 μs pulse width, 330 pps)	3.0 A
Reverse DC Voltage	3.0 V
Power Dissipation	100 mW ⁽³⁾
Output Transistor		
Collector-Emitter Voltage	25 V
Collector-Base Voltage	30 V
Emitter-Collector Voltage	5.0 V
Power Dissipation	150 mW ⁽⁴⁾

Notes:

- (1) Measured with input diode leads shorted together and output leads shorted together.
- (2) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering.
- (3) Derate linearly 1.33 mW/ $^\circ\text{C}$ above 25°C .
- (4) Derate linearly 2.0 mW/ $^\circ\text{C}$ above 25°C .

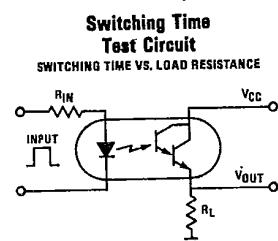
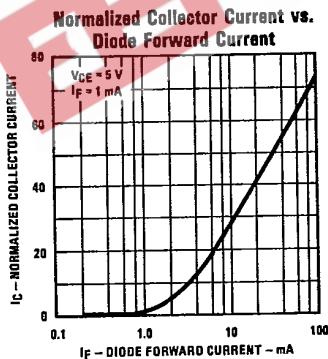
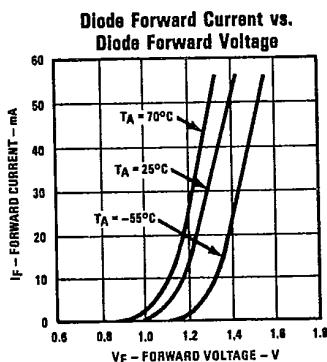
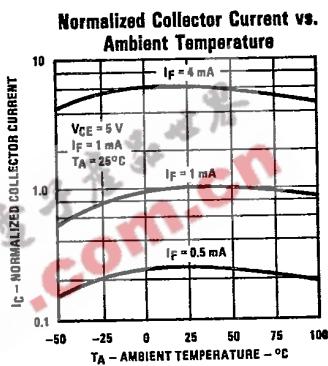
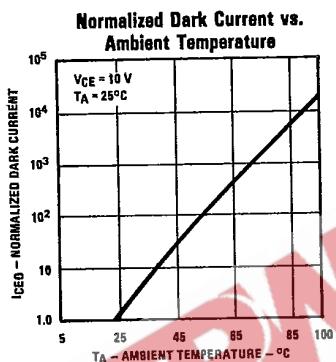
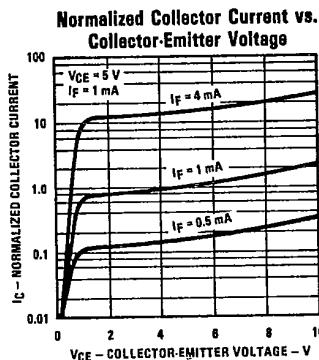
Types OPI3153, OPI3253

T-41-85 -

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Input Diode						
V_F	Forward Voltage			1.50	V	$I_F = 10.0 \text{ mA}$
I_R	Reverse Current			100	μA	$V_R = 3.0 \text{ V}$
Output Photosensor						
V_{BRICEO}	Collector-Emitter Breakdown Voltage	25			V	$I_C = 1.00 \text{ mA}$
V_{BRICBO}	Collector-Base Breakdown Voltage	30			V	$I_C = 100 \mu\text{A}$
V_{BREICO}	Emitter-Collector Breakdown Voltage	5.0			V	$I_E = 100 \mu\text{A}$
I_{CEO}	Collector-Emitter Dark Current			100	nA	$V_{CE} = 10.0 \text{ V}$
Coupled						
I_C/I_F	DC Current Transfer Ratio	500			%	$I_F = 1.00 \text{ mA}, V_{CE} = 5.0 \text{ V}$
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage		1.20		V	$I_F = 1.00 \text{ mA}, I_C = 1.00 \text{ mA}$
t_r	Output Rise Time	3.0			μs	$V_{CC} = 10.0 \text{ V}, I_C = 10.0 \text{ mA}, R_L = 100\Omega$
t_f	Output Fall Time	25			μs	See Test Circuit

Typical Performance Curves



NOTE: Rise Time (t_r) is time required for collector current to increase from 10% to 90% of its final value. Fall Time (t_f) is time required for the collector current to decrease from 90% to 10% of its initial value.